CLAIMS

1. A negative resist composition comprising:

a polymer having any one of dicarboxylate monoester compounds represented by the following general formulae (1) and (2) as a monomer component:

OH
$$R_4$$

$$R_5$$

$$R_2$$

$$OR_3$$

$$OR_3$$

HO
O
$$R_1$$
 R_2
 R_3
 R_4
 R_2
 R_3
 R_4
 R_2
 R_3
 R_4
 R_5
 R_4
 R_5
 R_6
 R_7
 R_8

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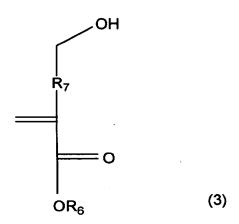
wherein, R_1 and R_2 represent alkyl chains having 0 to 8 carbon atoms, R_3 represents a substituent having at least two or more alicyclic structures, and R_4 and R_5 represent hydrogen atoms or alkyl groups having 1 to 8 carbon atoms; and

an acid generator which generates an acid by receiving light

irradiation.

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- 2. The negative resist composition according to claim 1, wherein said substituent having at least two or more alicyclic structures is at least one selected from the group consisting of adamantane, tricyclodecane, tetracyclodecane, isobornyl, norbornene, adamantane alcohol and norbornene lactone.
- 3. The negative resist composition according to claim 1, wherein said polymer is a copolymer of the dicarboxylate monoester compound and other monomer polymerizable with the dicarboxylate monoester compound.
- 4. The negative resist composition according to claim 3, wherein said other monomer polymerizable with the dicarboxylate monoester compound is at least one monomer represented by the following general formula (3):



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wherein, R_6 represents an alkyl group having 1 to 8 carbon atoms or a polycyclic hydrocarbon group, and R_7 represents an alkyl group having 1 to 8 carbon atoms.

25 5. A method of forming a resist pattern comprising the steps of:

forming a photoresist film on a substrate using said negative resist composition described in claim 1; and

forming a predetermined resist pattern on the substrate by applying an exposure treatment and a development treatment to the photoresist film.

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